




**HIGH SENSITIVITY DRY-DEVELOPABLE PHOTORESIST FOR DEEP UV**

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**Abstract of JP3152544**

**PURPOSE:** To enable dry development by using a phenol-aldehyde type condensation product and a photoactive compd. generating a strong acid which enables the reaction of hydroxy groups with an organometallic reagent when the compd. is exposed with deep UV.

**CONSTITUTION:** A phenol-aldehyde type condensation product represented by formula I and a radiation-degradable acid generating material such as a metallic or nonmetallic onium salt, a tosylate or a non-metal sulfonic acid precursor as a radiation sensitive material are used. In the formula I, R is H, -CH<sub>3</sub> or phenyl, R' is H, alkyl or aryl, R'' is H, halogen, nitro, alkoxy, alkyl, aryl or hydroxy and the basic arom. ring may be condensed with other cyclic structure so as to form a naphthol or anthracene unit. By such constitution, dry development is enabled.

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